# 2SD1511G

## Silicon NPN epitaxial planar type darlington

For low-frequency output amplification

#### ■ Features

- Forward current transfer ratio  $h_{FE}$  is designed high, which is appropriate to the driver circuit of motors and printer hammer:  $h_{FE} = 4000$  to 20000.
- A shunt resistor is omitted from the driver.
- Mini power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

### ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	100	V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	80	V
Emitter-base voltage (Collector open)	$V_{EBO}$	5	V
Collector current	$I_{C}$	1	A
Peak collector current	$I_{CP}$	1.5	A
Collector power dissipation *	P <sub>C</sub>	1	W
Junction temperature	$T_{j}$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

Note) \*: Printed circuit board: Copper foil area of 1 cm<sup>2</sup> or more, and the board thickness of 1.7 mm for the collector portion

#### Package

- CodeMiniP3-F2
- Pin Name
  - 1: Base
- 2: Collector
- 3: Emitter
- Marking Symbol: P

#### ■ Internal Connection

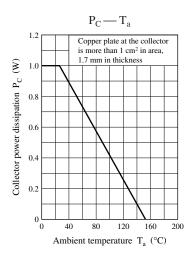
### ■ Electrical Characteristics $T_a = 25$ °C $\pm 3$ °C

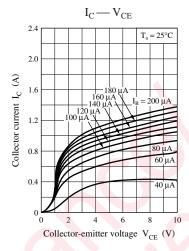
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_C = 100  \mu A, I_E = 0$	100			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = 1 \text{ mA}, I_B = 0$	80			V
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	$I_E = 100  \mu A, I_C = 0$	5			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 25 \text{ V}, I_{E} = 0$			100	nA
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 4 \text{ V}, I_{C} = 0$			100	nA
Forward current transfer ratio *1, 2	h <sub>FE</sub>	$V_{CE} = 10 \text{ V}, I_{C} = 1 \text{ A}$	4000		40 000	
Collector-emitter saturation voltage *1	V <sub>CE(sat)</sub>	$I_C = 1 \text{ A}, I_B = 1 \text{ mA}$			1.8	V
Base-emitter saturation voltage *1	V <sub>BE(sat)</sub>	$I_C = 1 \text{ A}, I_B = 1 \text{ mA}$			2.2	V
Transition frequency	$f_T$	$V_{CB} = 10 \text{ V}, I_{E} = -50 \text{ mA}, f = 200 \text{ MHz}$		150		MHz

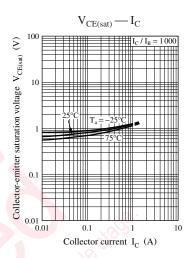
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

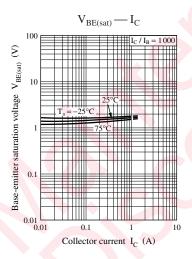
- 2. \*1: Pulse measurement
  - \*2: Rank classification

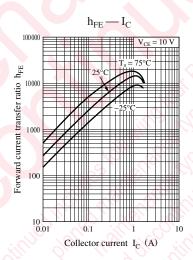
Rank	Q	Q R	
$h_{FE}$	4000 to 10000	8 000 to 20 000	16 000 to 40 000

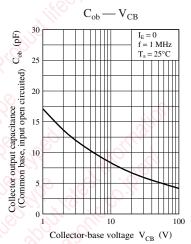






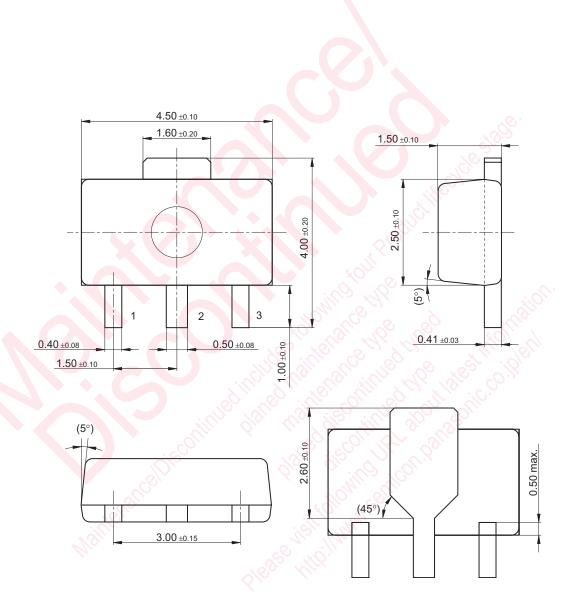






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MiniP3-F2 Unit: mm



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